

IN THE CLAIMS:

Please cancel Claims 1 to 3, 5 to 10, 14 to 16, 19, and 20 without prejudice to or disclaimer of the subject matter presented therein. Please amend Claims 11 to 13 as shown below.

1 to 10. (Cancelled)

11. (Currently Amended) The An organic semiconductor element according to claim 1, comprising a gate electrode, a gate insulating layer, an organic semiconductor layer, source/drain electrodes and a protective film which are provided on a surface of a substrate, wherein the organic semiconductor element further comprises an island-shaped protrusion layer having dispersed and island-shaped protrusions with a low surface energy, wherein the island-shaped protrusion layer is formed by spin coating or spray coating, the organic semiconductor layer is formed after forming the island-shaped protrusion layer, and the organic semiconductor layer is in contact with the island-shaped protrusions, and wherein the island-shaped protrusions with the low surface energy are made of polyamide or polyimide.

12. (Currently Amended) The An organic semiconductor element according to claim 1, comprising a gate electrode, a gate insulating layer, an organic semiconductor layer, source/drain electrodes and a protective film which are provided on a surface of a substrate, wherein the organic semiconductor element further comprises an island-shaped

protrusion layer having dispersed and island-shaped protrusions with a low surface energy,
wherein the island-shaped protrusion layer is formed by spin coating or spray coating, the
organic semiconductor layer is formed after forming the island-shaped protrusion layer, and
the organic semiconductor layer is in contact with the island-shaped protrusions, and
wherein the island-shaped protrusions with the low surface energy are made of a
fluorine-based polymer selected from the group consisting of polyfumarate-based polymers
and cyclic perfluoropolymers.

13. (Currently Amended) The An organic semiconductor element according
to claim 1, comprising a gate electrode, a gate insulating layer, an organic semiconductor
layer, source/drain electrodes and a protective film which are provided on a surface of a
substrate, wherein the organic semiconductor element further comprises an island-shaped
protrusion layer having dispersed and island-shaped protrusions with a low surface energy,
wherein the island-shaped protrusion layer is formed by spin coating or spray coating, the
organic semiconductor layer is formed after forming the island-shaped protrusion layer, and
the organic semiconductor layer is in contact with the island-shaped protrusions, and
wherein the island-shaped protrusions with the low surface energy are made of a
fluorine-based compound selected from the group consisting of fluoroalkylsilane
compounds and perfluoroether based compounds.

14 to 16. (Cancelled)

17. (Previously Presented) A production method of an organic semiconductor element, comprising providing on a surface of a substrate a gate electrode, a gate insulating layer, an organic semiconductor layer, source/drain electrodes and a protective film, wherein the method further comprises providing on the surface of the substrate an island-shaped protrusion layer having dispersed and island-shaped protrusions with a low surface energy, and wherein the island-shaped protrusions are formed in a dispersed manner by spin coating or spray coating, the organic semiconductor layer is formed after forming the island-shaped protrusion layer, and the organic semiconductor layer is formed in contact with the island-shaped protrusions.

18. (Original) The production method according to claim 17, wherein after forming the island-shaped protrusion layer having the dispersed and island-shaped protrusions with the low surface energy, which are formed by the spin coating or spray coating, the organic semiconductor layer is formed on the island-shaped protrusion layer under a heating condition of 60°C to 200°C.

19 and 20. (Cancelled)